L Number	Hits	Search Text	DB	Time stamp
1	1	(semiconductor or semiconductive) and	USPAT;	2004/02/20 11:40
		(organic with (insulat\$4 or dielectric)) and	US-PGPUB;	,,
		ethyne and (UV same (heat or heating or	EPO; JPO;	
		heated or anneal or annealing or annealed or	DERWENT;	
		bake or baking or baked))	IBM_TDB	
2	24	I	USPAT;	2004/02/20 11:41
		(organic with (insulat\$4 or dielectric)) and	US-PGPUB;	
		SILK and (UV same (heat or heating or heated	EPO; JPO;	
		or anneal or annealing or annealed or bake	DERWENT;	
		or baking or baked))	IBM_TDB	
3	3	(USPAT;	2004/02/20 11:46
		(organic with (insulat\$4 or dielectric)) and	US-PGPUB;	
		SILK and (UV same (heat or heating or heated	EPO; JPO;	
		or anneal or annealing or annealed or bake	DERWENT;	
		or baking or baked) same polymeriz\$5)	IBM_TDB	2004/02/20 22 22
4	64	(semiconductor or semiconductive) and	USPAT;	2004/02/20 13:10
		(organic with (insulat\$4 or dielectric)) and	US-PGPUB;	
		(UV same (heat or heating or heated or	EPO; JPO;	
	-	anneal or annealing or annealed or bake or	DERWENT;	
5	45	baking or baked) same polymeriz\$5) ((semiconductor or semiconductive) and	IBM_TDB USPAT;	2004/02/20 11:47
	1	(organic with (insulat\$4 or dielectric)) and	US-PGPUB;	2004/02/20 11:4/
ļ		(UV same (heat or heating or heated or	EPO; JPO;	
ļ ļ		anneal or annealing or annealed or bake or	DERWENT;	
		baking or baked) same polymeriz\$5)) and	IBM TDB	
		(monomer or oligomer)		
6	6	((thin adj film) or TFT) and (organic with	USPAT;	2004/02/20 13:09
ļ		(insulat\$4 or dielectric)) and (UV same	US-PGPUB;	,,,
		(heat or heating or heated or anneal or	EPO; JPO;	
		annealing or annealed or bake or baking or	DERWENT;	
ļ		baked) same polymeriz\$5) and (SILK or	IBM_TDB	
1		"GX-3")		
7	9	(organic with (insulat\$4 or dielectric)) and	USPAT;	2004/02/20 13:10
1		(UV same (heat or heating or heated or	US-PGPUB;	
1		anneal or annealing or annealed or bake or	EPO; JPO;	
1 j		baking or baked) same polymeriz\$5) and (SILK	DERWENT;	
1	_	or "GX-3")	IBM_TDB	0004/00/00 == ==
8	3	((organic with (insulat\$4 or dielectric))	USPAT;	2004/02/20 13:09
		and (UV same (heat or heating or heated or	US-PGPUB;	
		anneal or annealing or annealed or bake or baking or baked) same polymeriz\$5) and (SILK	EPO; JPO;	
1		or "GX-3")) not (((thin adj film) or TFT)	DERWENT; IBM TDB	
1		and (organic with (insulat\$4 or dielectric))	10.7_106	
1		and (UV same (heat or heating or heated or		
1		anneal or annealing or annealed or bake or		
'		baking or baked) same polymeriz\$5) and (SILK		
'		or "GX-3"))		
9	62	(organic with (insulat\$4 or dielectric)) and	USPAT;	2004/02/20 13:12
		(UV and (heat or heating or heated or anneal	US-PGPUB;	
		or annealing or annealed or bake or baking	EPO; JPO;	
'		or baked) and polymeriz\$5) and (SILK or	DERWENT;	
		"GX-3")	IBM_TDB	
10	24	((organic with (insulat\$4 or dielectric))	USPAT;	2004/02/20 13:19
		and (UV and (heat or heating or heated or	US-PGPUB;	
		anneal or annealing or annealed or bake or	EPO; JPO;	
		baking or baked) and polymeriz\$5) and (SILK	DERWENT;	
1.1	0510	or "GX-3")) not (silk adj screen\$4)	IBM_TDB	0004/00/00 55 55
11	2510	((438/758) or (438/780-781) or	USPAT;	2004/02/20 16:09
		(438/789-790)).CCLS.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
12	53	(((438/758) or (438/780-781) or	IBM_TDB USPAT;	2004/02/20 13:25
14	53	((438/789-790)).CCLS.) and (SILK or "GX-3")	US-PGPUB;	2004/02/20 13:25
		(450) 109-190) .CCEG. AMA (SIER OF "GY-3")	EPO; JPO;	
			DERWENT;	
			IBM TDB	

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13	2	((((==, ,==, ==, ==, ==, ==, ==, ==, ==	USPAT;	2004/02/20 13:26
		(438/789-790)).CCLS.) and (SILK or "GX-3"))	US-PGPUB;	
		and ((UV or ultraviolet) with polymeriz\$6)	EPO; JPO;	
			DERWENT;	
	1	(,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	IBM_TDB	
14	8	(((438/758) or (438/780-781) or	USPAT;	2004/02/20 14:37
		(438/789-790)).CCLS.) and (organic with	US-PGPUB;	
		(insulat\$4 or dielectric)) and ((UV or	EPO; JPO;	
		ultraviolet) with polymeriz\$6)	DERWENT;	
			IBM_TDB	
15	42	(, (<u>-</u>	USPAT;	2004/02/20 14:38
[cure or curing or anneal or annealing or	US-PGPUB;	
		bake or baking) with polymer\$8 with (low adj	EPO; JPO;	
		temperature)	DERWENT;	
			IBM_TDB	
16	0	, ,,,, ,,, ,,,,,,,,,,,,,,,,,,,,,,,,,,,,	USPAT;	2004/02/20 14:39
		or cure or curing or anneal or annealing or	US-PGPUB;	
1		bake or baking) with polymer\$8 with (low adj	EPO; JPO;	
1		temperature)) and (SILK) not (silk adj	DERWENT;	
		screen\$4)	IBM_TDB	
17	→ 0	((UV or ultraviolet) with (heat or heating	USPAT;	2004/02/20 14:39
		or cure or curing or anneal or annealing or	US-PGPUB;	
		bake or baking) with polymer\$8 with (low adj	EPO; JPO;	
		temperature)) and (organic with	DERWENT;	
		(insultati\$4 or dielectric))	TBM_TDB	ĺ
18	2	((UV or ultraviolet) with (heat or heating	USPAT;	2004/02/20 15:06
		or cure or curing or anneal or annealing or	US-PGPUB;	
i		bake or baking) with polymer\$8 with (low adj	EPO; JPO;	
		temperature)) and (organic with precursor)	DERWENT;	
			IBM_TDB	
19	6548	(438/149-166).CCLS.	USPAT;	2004/02/20 15:07
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
20	41	((438/149-166).CCLS.) and (transparent with	USPAT;	2004/02/20 15:09
		substrate) and matrix.ti. and (gate with	US-PGPUB;	
		line) and electrode\$1 and (source with line)	EPO; JPO;	
		and (source with electrode\$1) and (pixel	DERWENT;	
		with electrodes)	IBM_TDB	
21	9	(((438/149-166).CCLS.) and (transparent with	USPAT;	2004/02/20 15:09
		substrate) and matrix.ti. and (gate with	US-PGPUB;	
		line) and electrode\$1 and (source with line)	EPO; JPO;	
	1	and (source with electrode\$1) and (pixel	DERWENT;	
		with electrodes)) and (organic with	IBM_TDB	
		(dielectric or insulati\$4))		4 . 4
22	2	("4756977").PN.	USPAT;	2004/02/20 16:10
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	